

BUK6210-55C

N-channel TrenchMOS intermediate level FET

Rev. 2 — 4 October 2010

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u>	-	-	78	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	128	W
Static chara	Static characteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 11}{\text{ constant}}$	-	8.1	9.6	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 78 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	94	mJ
Dynamic ch	Dynamic characteristics					
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}$; $V_{DS} = 44 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	-	19.5	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	D
3	S	source		$G \longrightarrow A$
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6210-55C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V_{GS}	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	78	Α
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	55	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; t_p ≤ 10 μs; pulsed; see <u>Figure 3</u>		-	311	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	128	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					
Is	source current	$T_{mb} = 25 ^{\circ}C$		-	78	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	311	Α
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 78 A; V_{sup} \leq 55 V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	94	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy		[3][4][5]	-	-	J

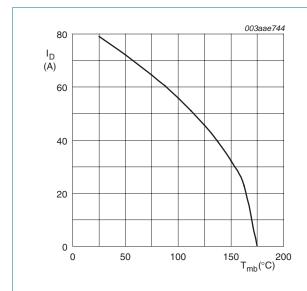
^{[1] -16}V accumulated duration not to exceed 168 hrs

^[2] Accumulated pulse duration not to exceed 5mins.

^[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

^[4] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[5] Refer to application note AN10273 for further information.

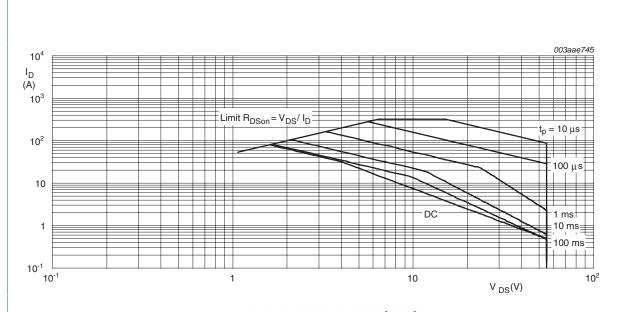


120
Pder (%)
80

40 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 1. Continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



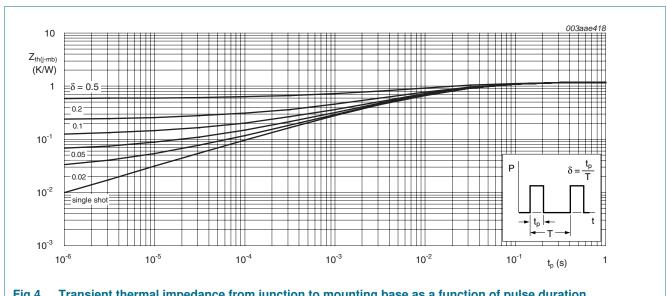
 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.17	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	55	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	3.3	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 10</u>	8.0	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	8.1	9.6	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	9.9	13.2	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11	-	10.8	14.5	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	21.2	mΩ
Dynamic c	and the second s					
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 44 \text{ V}$; $V_{GS} = 5 \text{ V}$; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	34.4	-	nC
			-	34.4	-	nC nC
		see <u>Figure 13</u> ; see <u>Figure 14</u> I _D = 25 A; V _{DS} = 44 V; V _{GS} = 10 V;	-		-	
$Q_{G(tot)}$	total gate charge	see <u>Figure 13</u> ; see <u>Figure 14</u> $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u> $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	63		nC
Q _{G(tot)} Q _{GS} Q _{GD}	total gate charge gate-source charge	see Figure 13; see Figure 14 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14 $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	63	-	nC nC
Q _{G(tot)} Q _{GS} Q _{GD}	total gate charge gate-source charge gate-drain charge	see Figure 13; see Figure 14 $I_D = 25 \text{ A}$; $V_{DS} = 44 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14 $I_D = 25 \text{ A}$; $V_{DS} = 44 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13 $I_D = 25 \text{ A}$; $V_{DS} = 44 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	-	63 10.4 19.5	-	nC nC
Q _G (tot) Q _{GS} Q _{GD} C _{iss} C _{oss}	gate-source charge gate-drain charge input capacitance	see Figure 13; see Figure 14 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14 $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	63 10.4 19.5 2990	- 4000	nC nC nC
Q _{G(tot)} Q _{GS} Q _{GD} C _{iss}	gate-source charge gate-drain charge input capacitance output capacitance reverse transfer	see Figure 13; see Figure 14 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ see Figure 13 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $V_{GS} = 0 \text{ V; } V_{DS} = 25 \text{ V; } f = 1 \text{ MHz; }$ $T_{j} = 25 \text{ °C; see Figure 15}$ $V_{DS} = 45 \text{ V; } R_{L} = 1.8 \text{ \Omega; } V_{GS} = 10 \text{ V; }$	- - -	63 10.4 19.5 2990 290	- - 4000 350	nC nC nC
Q _G (tot) Q _{GS} Q _{GD} C _{iss} C _{oss} C _{rss}	gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance	see Figure 13; see Figure 14 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13 $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14 $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see Figure 15}$	- - -	63 10.4 19.5 2990 290 205	- 4000 350 281	nC nC pF pF pF
$Q_{G(tot)}$ Q_{GS} Q_{GD} C_{iss} C_{oss} C_{rss} $t_{d(on)}$ t_r	gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time	see Figure 13; see Figure 14 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ see Figure 13 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $V_{GS} = 0 \text{ V; } V_{DS} = 25 \text{ V; } f = 1 \text{ MHz; }$ $T_{j} = 25 \text{ °C; see Figure 15}$ $V_{DS} = 45 \text{ V; } R_{L} = 1.8 \text{ \Omega; } V_{GS} = 10 \text{ V; }$	- - -	63 10.4 19.5 2990 290 205	- 4000 350 281	nC nC pF pF pF
Q _G (tot) Q _{GS} Q _{GD} C _{iss} C _{oss} C _{rss} t _{d(on)}	gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time	see Figure 13; see Figure 14 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ see Figure 13 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $V_{GS} = 0 \text{ V; } V_{DS} = 25 \text{ V; } f = 1 \text{ MHz; }$ $T_{j} = 25 \text{ °C; see Figure 15}$ $V_{DS} = 45 \text{ V; } R_{L} = 1.8 \text{ \Omega; } V_{GS} = 10 \text{ V; }$	- - -	63 10.4 19.5 2990 290 205 16 45	- 4000 350 281 -	nC nC pF pF pF ns ns
$Q_{G(tot)}$ Q_{GS} Q_{GD} C_{iss} C_{oss} C_{rss} $t_{d(on)}$ t_r $t_{d(off)}$	gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time	see Figure 13; see Figure 14 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ see Figure 13 $I_{D} = 25 \text{ A; } V_{DS} = 44 \text{ V; } V_{GS} = 10 \text{ V; }$ $\text{see Figure 13; see Figure 14}$ $V_{GS} = 0 \text{ V; } V_{DS} = 25 \text{ V; } f = 1 \text{ MHz; }$ $T_{j} = 25 \text{ °C; see Figure 15}$ $V_{DS} = 45 \text{ V; } R_{L} = 1.8 \text{ \Omega; } V_{GS} = 10 \text{ V; }$	- - - - -	63 10.4 19.5 2990 290 205 16 45 130	- 4000 350 281 - -	nC nC pF pF pF ns ns ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 16</u>	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	48	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}$	-	88	-	nC

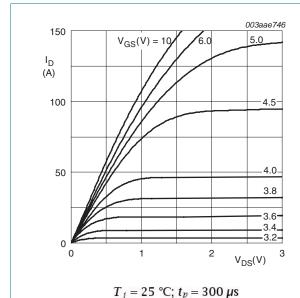


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

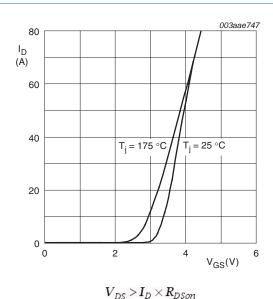


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

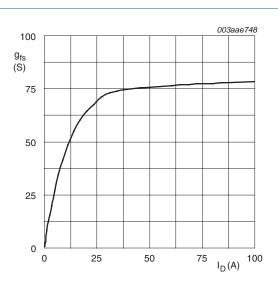
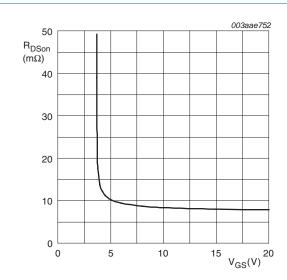


Fig 6. Forward transconductance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}\text{C}; V_{DS} = 15 \,^{\circ}\text{V}$



 $T_j = 25$ °C; $I_D = 15$ A

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

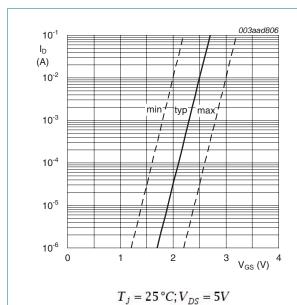


Fig 9. Sub-threshold drain current as a function of gate-source voltage

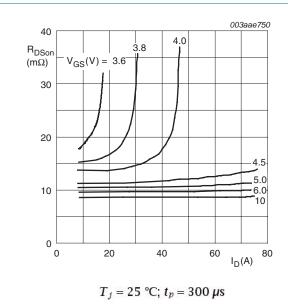


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

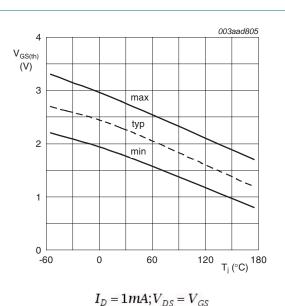


Fig 10. Gate-source threshold voltage as a function of junction temperature

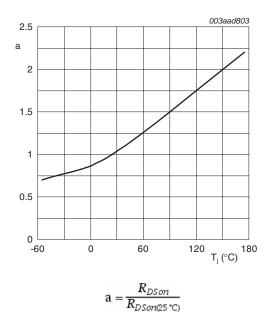


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

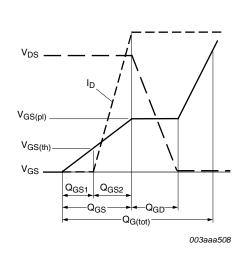


Fig 13. Gate charge waveform definitions

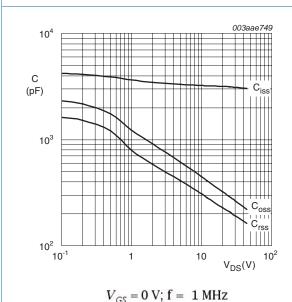
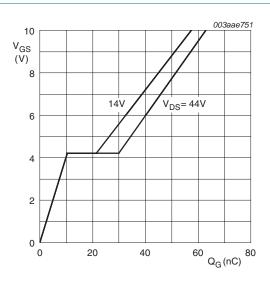


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25$ °C; $I_D = 25$ A

Fig 14. Gate-source voltage as a function of gate charge; typical values

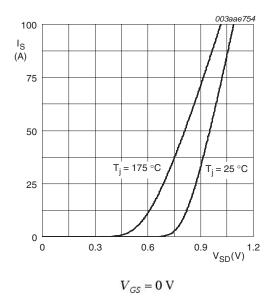


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

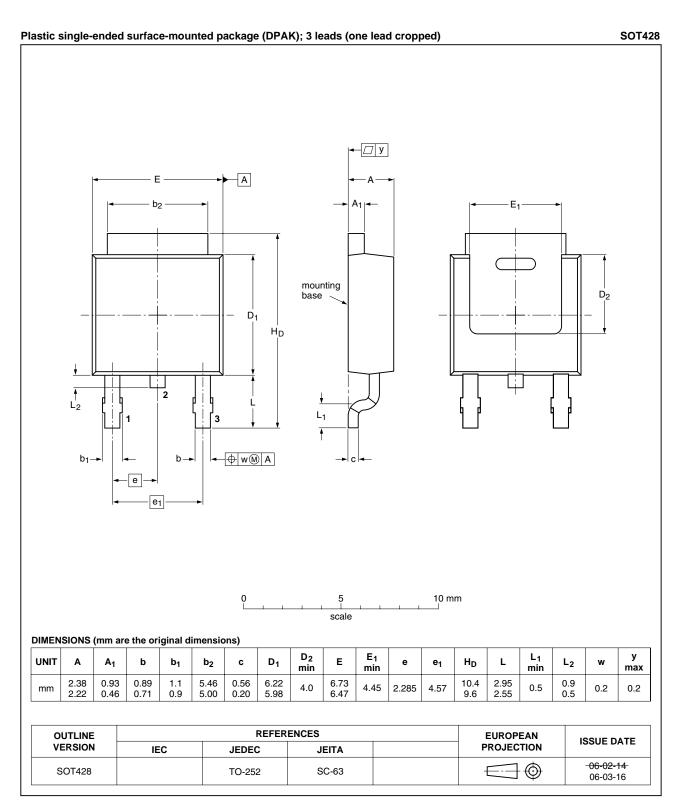


Fig 17. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6210-55C v.2	20101004	Product data sheet	-	BUK6210-55C v.1
Modifications:	 Status change 	ed from objective to product.		
BUK6210-55C v.1	20100907	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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10. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

BUK6210-55C

Nexperia

N-channel TrenchMOS intermediate level FET

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